## P & N-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
$V_{DS}(V)$	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$			
30	$32 @ V_{GS} = 10V$	4.3			
	$46 @ V_{GS} = 4.5V$	3.7			
20	$52 @ V_{GS} = -10V$	-3.8			
-30	$80 @ V_{GS} = -4.5V$	-2.8			

- $\begin{array}{ll} \bullet & \quad Low \; r_{DS(on)} \; provides \; higher \; efficiency \; and \\ extends \; battery \; life \\ \end{array}$
- Low thermal impedance copper leadframe TSSOP-8 saves board space
- Fast switching speed
- High performance trench technology

_	TSSOP-8 Top View		$D_1$	$S_2$
D1 2	1	8	G <sub>1</sub>	$G_2$
S1	3 4	6	$\overset{\Diamond}{S_1}$ N-Channel MOSFET	D <sub>2</sub> P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter			N-Channel	P-Channel	Units	
Drain-Source Voltage			30	-30	V	
Gate-Source Voltage			±20	±20	V	
Continuos Due in Commenta	T <sub>A</sub> =25°C	Ţ	4.3	-3.8	A	
Continuous Drain Current <sup>a</sup>	$T_A=25$ °C $T_A=70$ °C	<sup>1</sup> D	3.5	-3.0		
Pulsed Drain Current <sup>b</sup>			20	-20		
Continuous Source Current (Diode Conduction) <sup>a</sup>			1.0	-1.0	A	
D D: : : a	$T_A=25^{\circ}C$	D	1.14	1.14	W	
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	<sup>1</sup> D	0.73	0.73	VV	
Operating Junction and Storage Temperature Range			-55 to 150	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Тур	Max			
Manimum Innation to Ambinta	t <= 10 sec	D	88	110	0C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	$R_{thJA}$	120	150	°C/W	

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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SPECIFICATIONS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Test Conditions	Limits			Unit		
	Symbol	Test Conditions	Ch	Min	Тур	Max	Umt	
Static								
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$ , $I_D = 250 \text{ uA}$	N	1.0			v	
Gute Threshold Voltage	▼ GS(th)	VGS - VDS, 1D230 uA		-1.0			·	
Gate-Body Leakage	$I_{GSS}$	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$ $V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$	N P			±100 ±100	nA	
Z C-t- V-1t Di Ct	T .		N			1		
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$	P			-1	uA	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	N	20			Α	
on state Brain carrent	D(oii)	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	P	-20		32	2.1	
		VGS = 10 V, I <sub>D</sub> = 4.3 A VGS = 4.5 V, I <sub>D</sub> = 3.7 A	N			46		
Drain-Source On-Resistance <sup>A</sup>	$r_{DS(on)}$	VGS = -10  V, Ip = -3.8  A				52	mΩ	
		VGS = -4.5  V, ID = -2.8  A	P			80		
Forward Tranconductance <sup>A</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}, I_{D} = 4.3 \text{ A}$ $V_{DS} = -15 \text{ V}, I_{D} = -3.8 \text{ A}$	N		11		S	
1 of ward 1 fanconductance	8ts	$V_{DS} = -15 \text{ V}, I_{D} = -3.8 \text{ A}$	P		11		٥	
Dynamic								
Total Gate Charge	Qg		N		4.7			
Total Gate Charge	Qg	N-Channel	P N		8.0			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15V, V_{GS} = 4.5V, I_{D} = 4.3A$			2.3		nC	
		P-Channel	P N		1.5		-	
Gate-Drain Charge	$Q_{gd}$	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.8A	P		4.5		1	
			N		13			
Turn-On Delay Time	t <sub>d(on)</sub>	N-Chaneel	P		14			
D: T:		$V_{DD}$ =15V, VGS=4.5V, ID=1A,	N		14			
Rise Time	$t_{\rm r}$	$R_{\text{GEN}}=6\Omega$ ,	P		14			
Turn-Off Delay Time	fı, m	P-Channel	N		30		nS	
Tuill-Off Delay Tille	td(off)	VDD=-15V, VGS=-4.5V, ID=-1A	P		40			
Fall-Time	$t_{\mathrm{f}}$	RGEN= $6\Omega$	N		30			
Tun Thie	LI LI		P		30			

## Notes

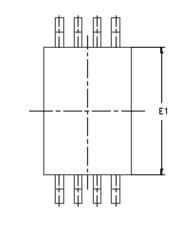
- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

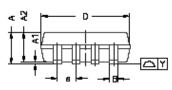
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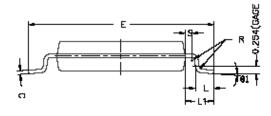
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## Package Information

TSSOP-8: 8LEAD







DIM.	MILLIMETERS					
шм.	MIN.	NDM.	MAX.			
Α	1.05	1.10	1.20			
A(1)	0.05	0.10	0.15			
A(2)	99.0	1.02	1.05			
В	D.19	0.25	0.30			
С		0.127				
D	2.90	3.0D	3.10			
Ε	6.20	6.40	6.60			
E1	4.30	4.40	4.50			
В	0.65950					
L	0.45	0.60	0.75			
L1	0.90	1.00	1.10			
Y			0.10			
<b>8</b> 1	O.	4	Ē.			
R	D.09		- 1			
S	0.20					